Rev.H Jul.-2018

TO-220 N MOS N-CHANNEL MOSFET in a TO-220 Plastic Package.

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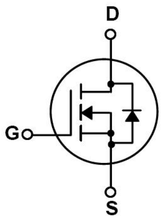
Low gate charge, low crss, fast switching.

DC/DC

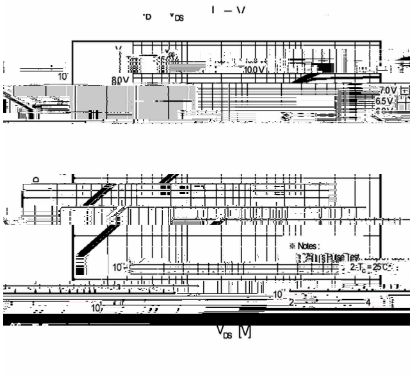
These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

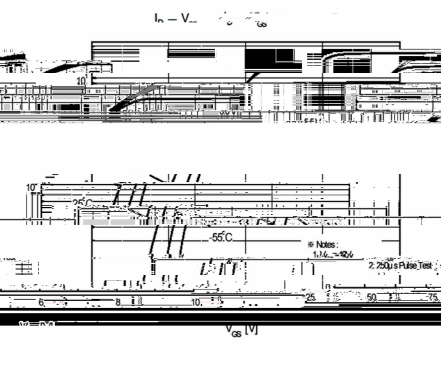


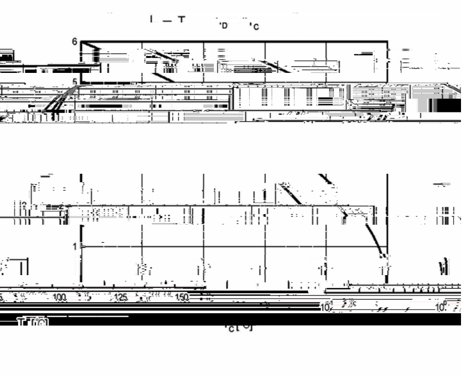
PIN1 G PIN 2 D PIN 3 S

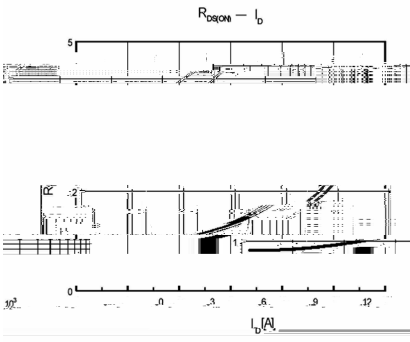
See Marking Instructions.

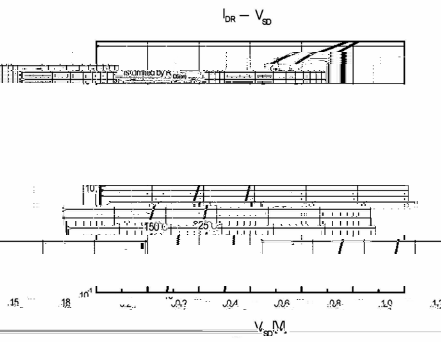
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	400	V
Drain Current	I_D(Tc=25)	6.0	A
	I_D(Tc=100)	3.6	A
Pulsed Drain Current	I_{DM}	24	A
Gate-Source Voltage	V_{GSS}	±30	V
Avalanche Current	I_{AR}	5.5	A
Single Pulsed Avalanche Energy	E_{AS}	390	mJ
Repetitive Avalanche Energy	E_{AR}	8.75	mJ
Total Power Dissipation	P_D(Tc=25)	87.5	W
Junction and Storage Temperature Range	T_J,T_{STG}	-55 to 150	R

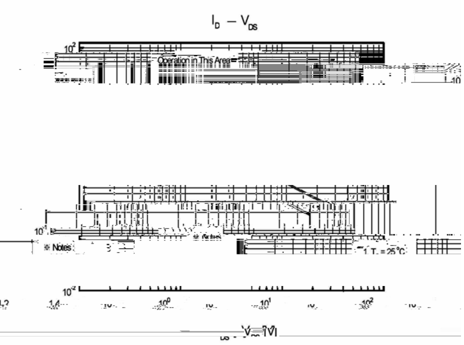

I_D — V_DS
10.0V
8.0V
7.0V
6.5V
V_DS [V]

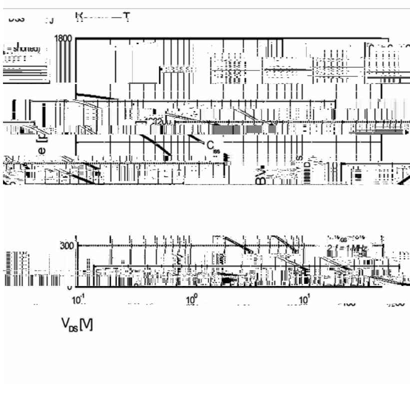

I_D — V_GS
25°C
-55°C
※ Notes :
2. 250µs Pulse Test
V_GS [V]

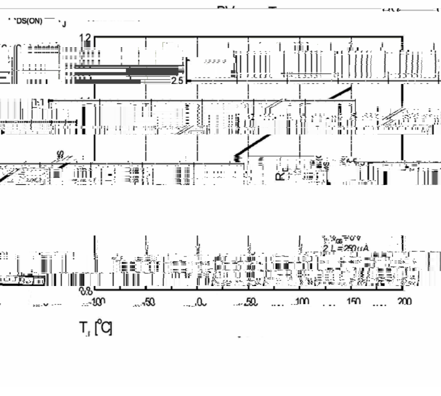

I_D — T_C
25
50
75
100
125
150
T_C [°C]

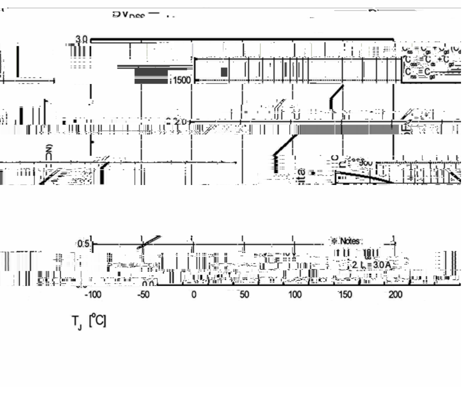

R_DS(ON) — I_D
5
0
I_D [A]


I_DR — V_SD
150°C
25°C
0.2
0.4
0.6
0.8
1.0
1.2
V_SD [V]


I_D — V_DS
Operation in This Area
※ Notes :
1. T_C = 25°C
V_DS [V]

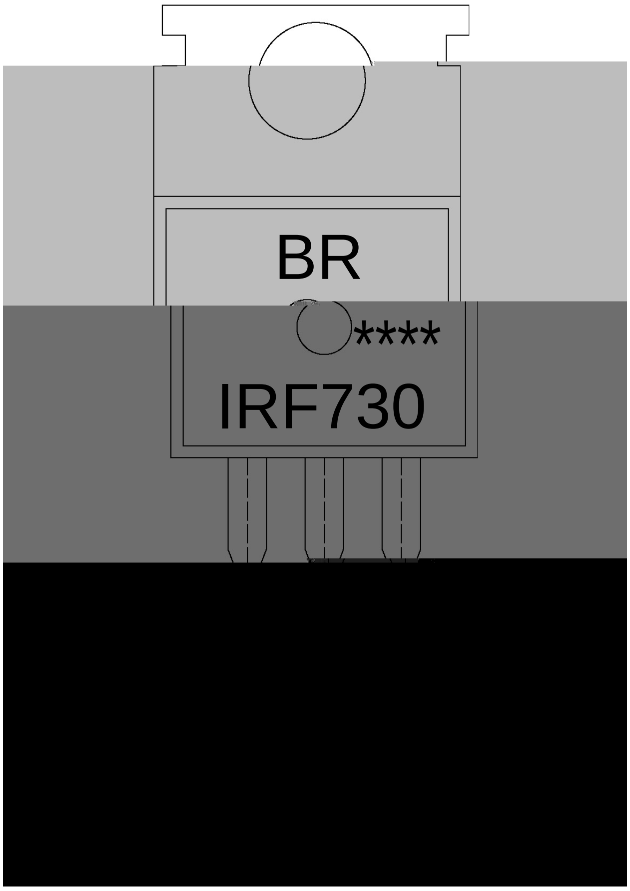

1800
300
0
C_iss
2. f = 1MHz
V_DS [V]


1.2
2. I_D = 250µA
-100
-50
0
50
100
150
200
T_J [°C]


3.0
2.5
0.5
0.0
※ Notes :
2. I_D = 30A
-100
-50
0
50
100
150
200
T_J [°C]

[redacted]

Symbol	Dimensions In Millimeters Min	Dimensions In Millimeters Max	Symbol	Dimensions In Millimeters Min	Dimensions In Millimeters Max
A	9.8	10.2	C	1.2	1.4
[illegible]	3.56	3.64	D	6.3	6.7
[illegible]	15.7	16.1	B1	9.0	9.4
[illegible]	2.6	3.61	[illegible]	2.6	[illegible]
[illegible]	8.6	10.6	[illegible]	0.7	0.9
[illegible]	0.4	0.6	[illegible]	[illegible]	[illegible]
[illegible]	[illegible]	[illegible]	[illegible]	[illegible]	[illegible]
[illegible]	1.45	[illegible]	Q2	1.25	[illegible]



BR

IRF730

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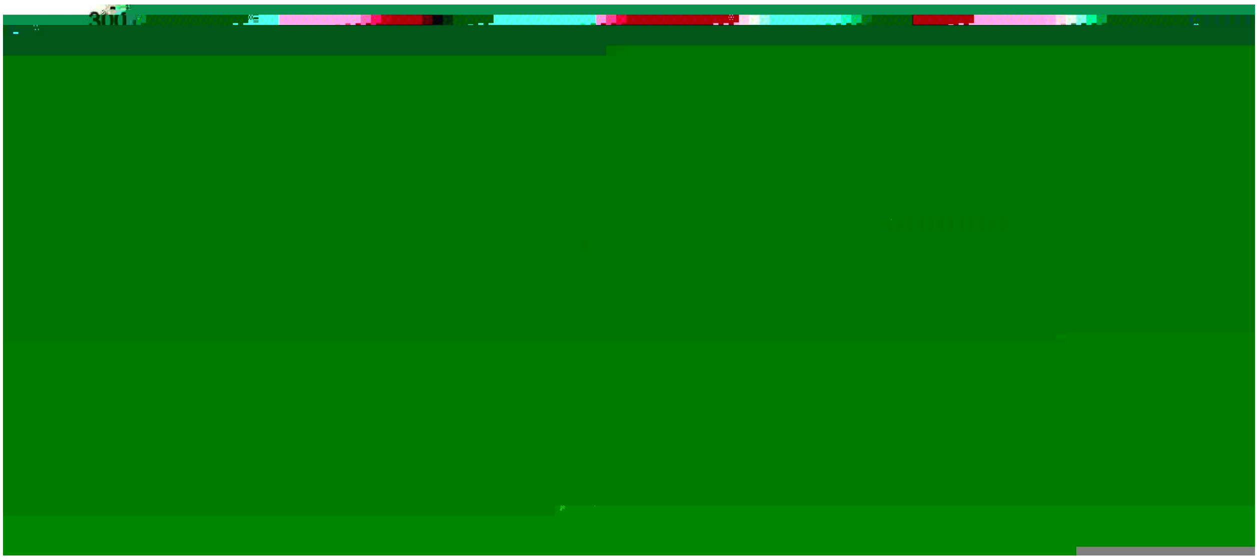
Note:

BR:	Company Code
IRF730:	Product Type.
****:	Lot No. Code, code change with Lot No.



1 25 150 60 90sec;

2 255±5 5±0.5sec;

3 2 10 /sec.

Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

270±5 10±1 sec.

Temp.:270±5 Time:10±1 sec

/ BULK

Package Type

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